Electronic supplementary information (ESI)

Epitaxtial lift-off for freestanding InGaN/GaN membrane and vertical blue light-emitting-diode

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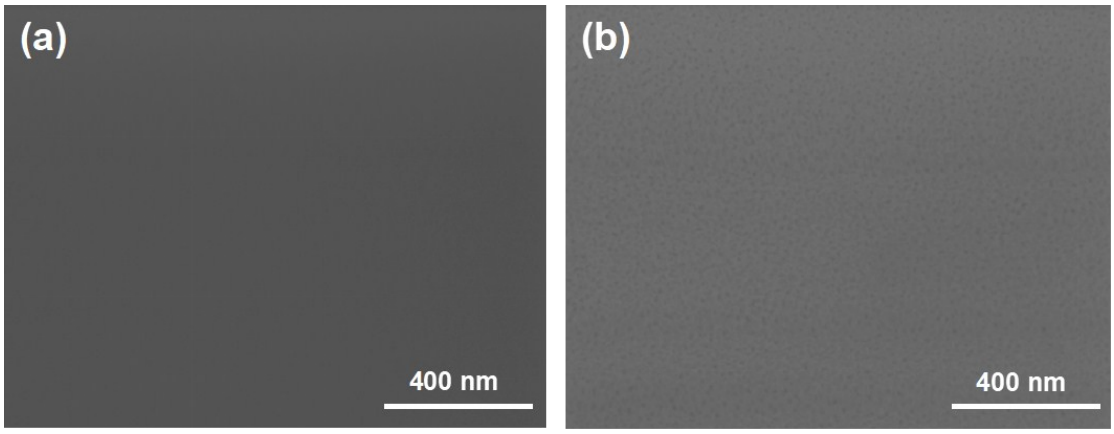

Fig. S1 The corresponding high-resolution SEM images for both the top (a) and bottom (b) surface of the transferred InGaN/GaN membranes LED.

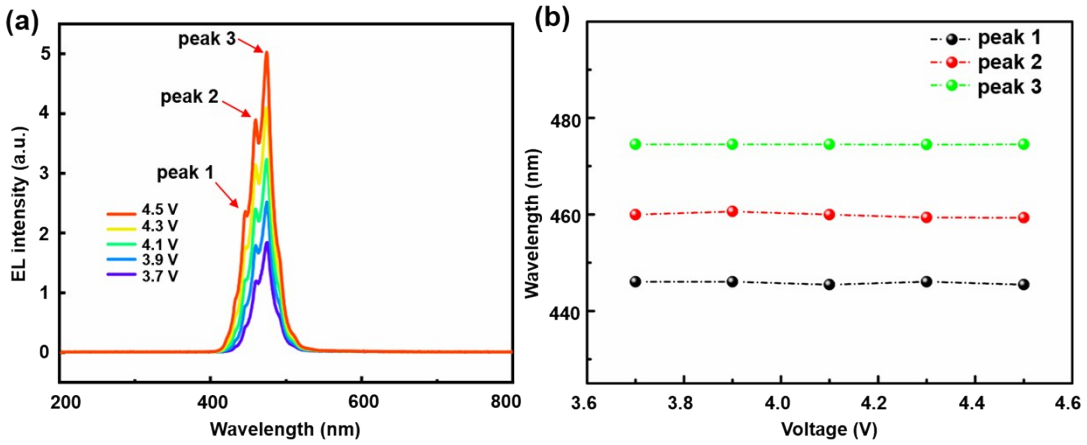

Fig. S2 The EL spectra from another different position of the membranes LED. (a) The EL spectra of freestanding InGaN/GaN membranes LED from another position. (b) The EL peak position changing of InGaN/GaN membranes LED.